

Automotive high efficiency ultrafast diode

Features

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- High junction temperature
- Low leakage current
- AEC-Q101 qualified

Description

Dual center tap rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in DPAK and D²PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection for automotive applications.

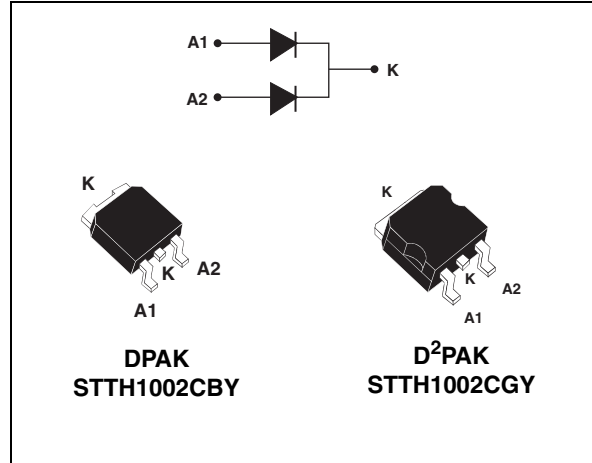


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	Up to 2 x 8 A
V_{RRM}	200 V
T_j (max)	175 °C
V_F (typ)	0.78 V
t_{rr} (typ)	20 ns

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			200	V
I _{F(RMS)}	Forward rms current		D ² PAK	20	A
			DPAK	10	
I _{F(AV)}	Avarage forward current δ = 0.5	T _c = 155 °C	Per diode	5	A
		T _c = 150 °C	Per device	10	
		T _c = 135 °C	Per diode	8	
		T _c = 125 °C	Per device	16	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal		50	A
T _{stg}	Storage temperature range			-65 to + 175	°C
T _j	Operating junction temperature range			-40 to + 175	°C

Table 3. Thermal parameters

Symbol	Parameter		Value (max)	Unit
$R_{th(j-c)}$	Junction to case	Per diode	4.0	$^{\circ}\text{C/W}$
		Per device	2.5	
$R_{th(j-c)}$	Coupling		1.0	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P(\text{diode1}) \times R_{th(j-c)} (\text{per diode}) + P(\text{diode2}) \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ }^{\circ}\text{C}$	$V_R = V_{RRM}$			5	μA
		$T_j = 125\text{ }^{\circ}\text{C}$			3	40	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ }^{\circ}\text{C}$	$I_F = 5\text{ A}$			1.1	V
		$T_j = 25\text{ }^{\circ}\text{C}$	$I_F = 10\text{ A}$			1.25	
		$T_j = 150\text{ }^{\circ}\text{C}$	$I_F = 5\text{ A}$		0.78	0.89	
		$T_j = 150\text{ }^{\circ}\text{C}$	$I_F = 10\text{ A}$			1.05	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.73 \times I_{F(AV)} + 0.032 I_{F(RMS)}^2$$

Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25\text{ }^{\circ}\text{C}$	$I_F = 1\text{ A}$ $V_R = 30\text{ V}$ $di_F/dt = 100\text{ A}/\mu\text{s}$		20	25	ns
I_{RM}	Reverse recovery current	$T_j = 125\text{ }^{\circ}\text{C}$	$I_F = 5\text{ A}$ $V_R = 160\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$		5.9	7.6	A
t_{fr}	Forward recovery time	$T_j = 25\text{ }^{\circ}\text{C}$	$I_F = 5\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			110	ns
V_{FP}	Forward recovery voltage	$T_j = 25\text{ }^{\circ}\text{C}$	$I_F = 5\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$		2.4		V

Figure 1. Peak current versus duty cycle (per diode)

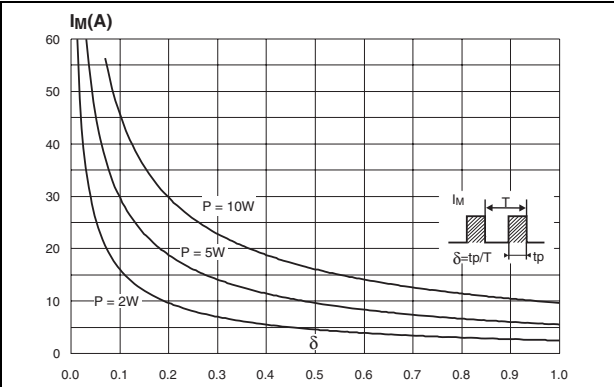


Figure 2. Forward voltage drop versus forward current (typical values, per diode)

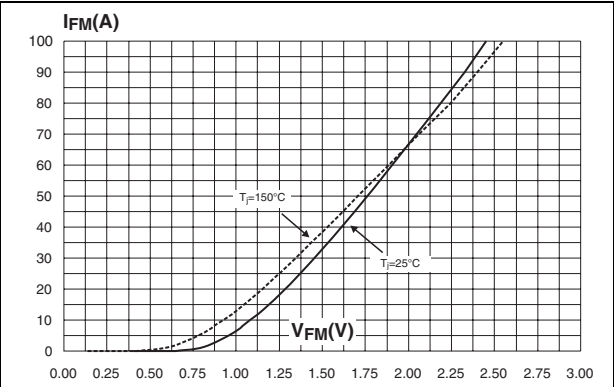


Figure 3. Forward voltage drop versus forward current (maximum values, per diode)

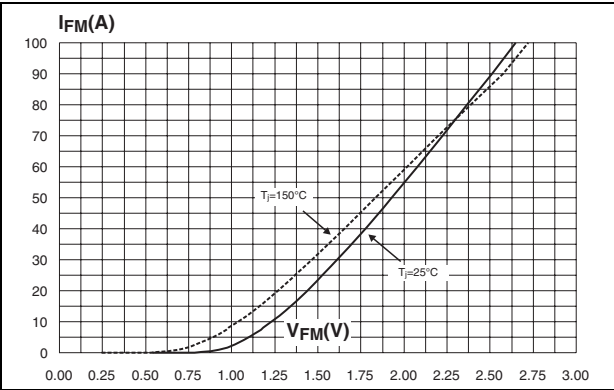


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

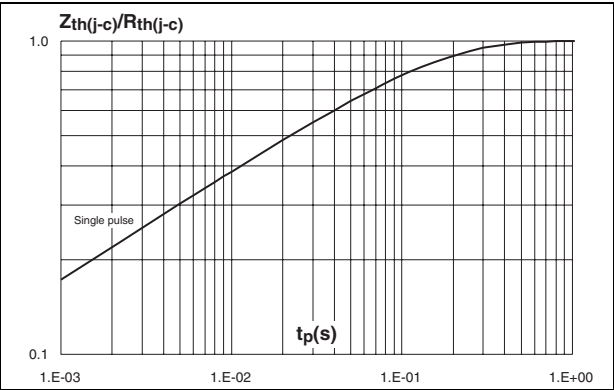


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

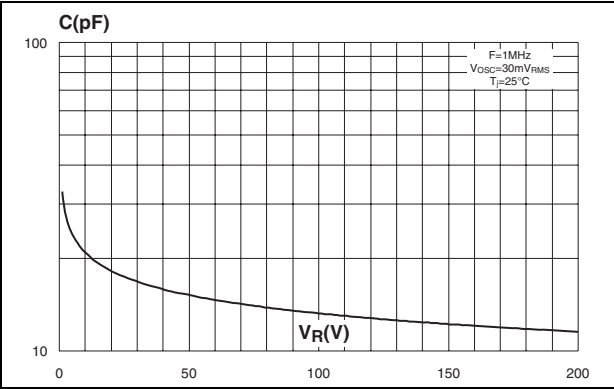
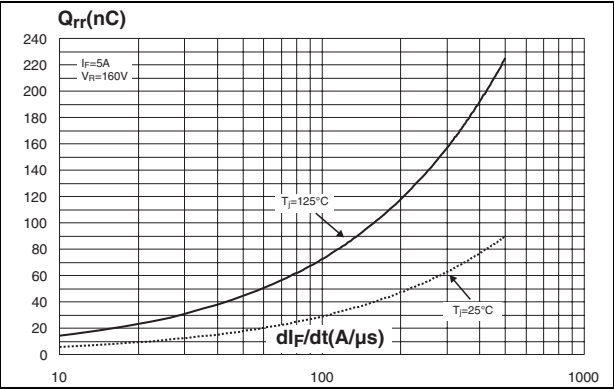


Figure 6. Reverse recovery charges versus dI_F/dt (typical values, per diode)



3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH1002CBY-TR	STTH1002CY	DPAK	0.3 g	2500	Tape and reel
STTH1002CGY-TR	STTH1002CGY	D ² PAK	1.48 g	1000	